

SGT N80-85V Power MOSFET

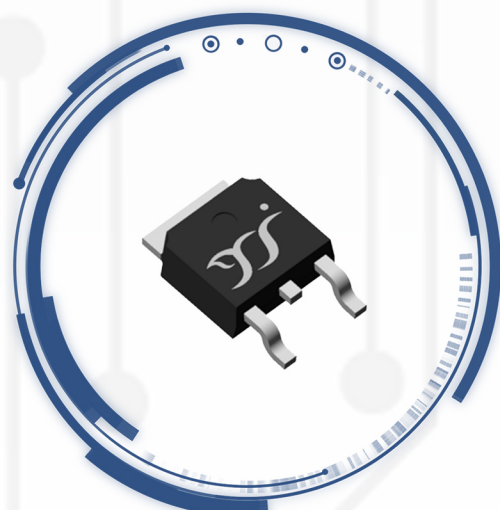
Yangjie Technology newly launched N80V-N85V series MOSFET products, using advanced SGT (Shield Gate Trench MOSFET) technology, designed for motor drive, BMS and other applications. This design optimize the performance of BVdss, Rdson, Qg,etc., and the same time improve the anti-inrush current capability of MOSFET.

N80V-N85V series MOSFET products have TO-220, TO-263, TO-252, PDFN5060 and other packages. Widely used in battery management systems, energy storage systems, inverter power supply systems, motor drive systems, power management systems, etc., which are the core power control components

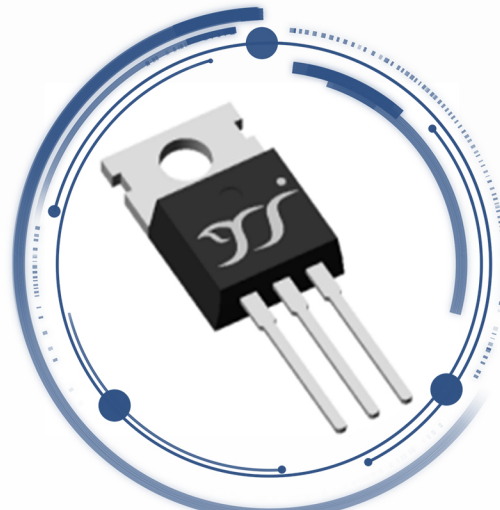
At present, Yangjie Technology has launched N40V, N60V, N80V-N85V, N100V, N120V and other SGT process series products to solve the needs of customers' various applications.



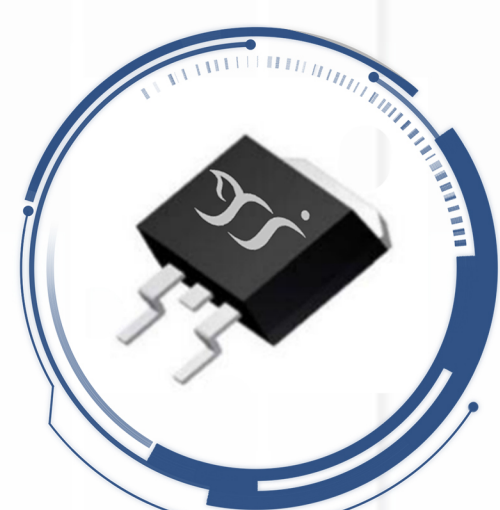
PDFN5060



TO-252



TO-220



TO-263

Product Features

- 1.The use of SGT process, bring very low Rdson and excellent switching characteristics result in lower FOM and reduced system losses.
- 2.Compared with the traditional Trench process, the parameter of Ciss/Qg has been greatly optimized, and there are more choices when designing MOSFET drivers.
- 3.According to various abnormal working states in system applications, the EAS characteristics of MOS products are optimized to improve system reliability.

Electrical parameters

Product Name	Package	BVdss	I_D	Vgs(th)	Rdson@10V	Qg
		(V)	(A)	Typ.(V)	Typ.(mΩ)	Typ.(nC)
YJG100G08A	PDFN5060	80	100	3	3.6	73
YJG100G08E	PDFN5060	80	100	1.8	3.6	90
YJD110G08A	TO-252	80	110	1.8	4.2	95
YJP120G08A	TO-220	80	120	3	3.9	73
YJB120G08A	TO-263	80	120	3	3.6	73
YJP118G08H	TO-220	85	118	3	5	62
YJB118G08H	TO-263	85	118	3	4.5	63

Application

PD power supply
Inverter power supply
Lithium battery BMS
Motor driver

